

01R00422

FIG. 1

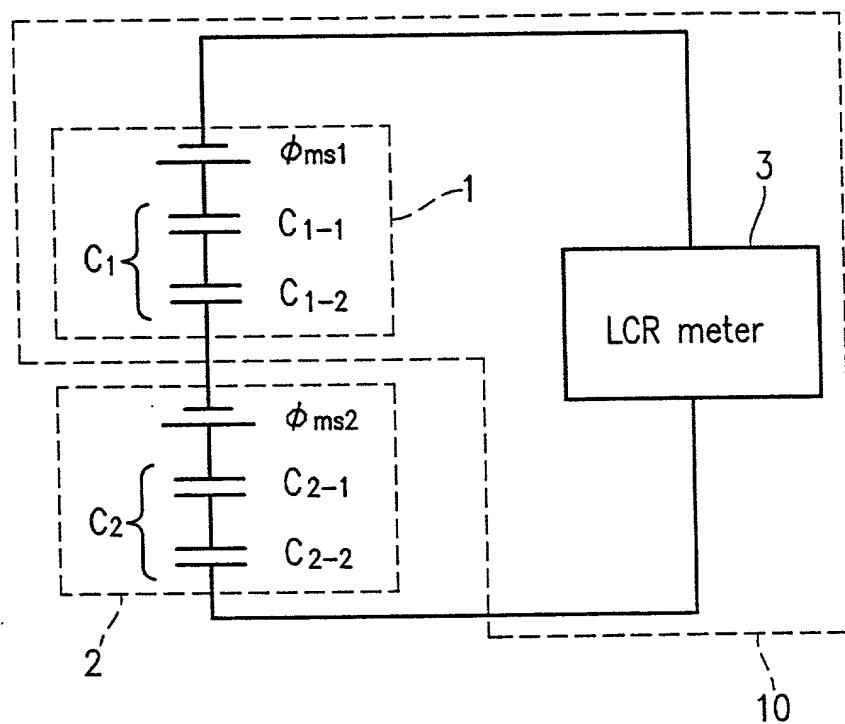


FIG. 2

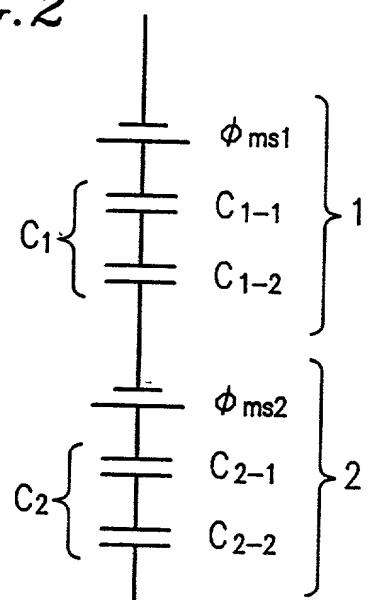


FIG.3

NMOS C-V Characteristics

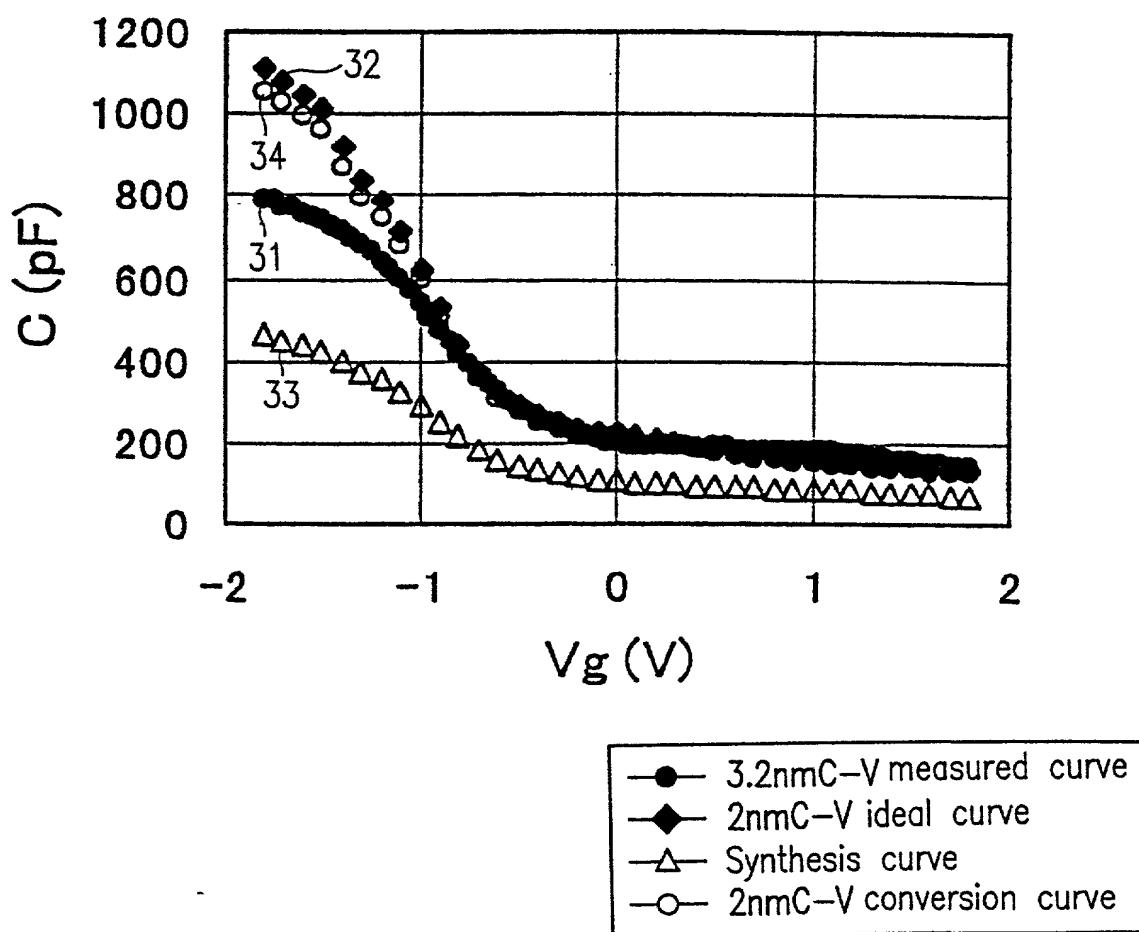
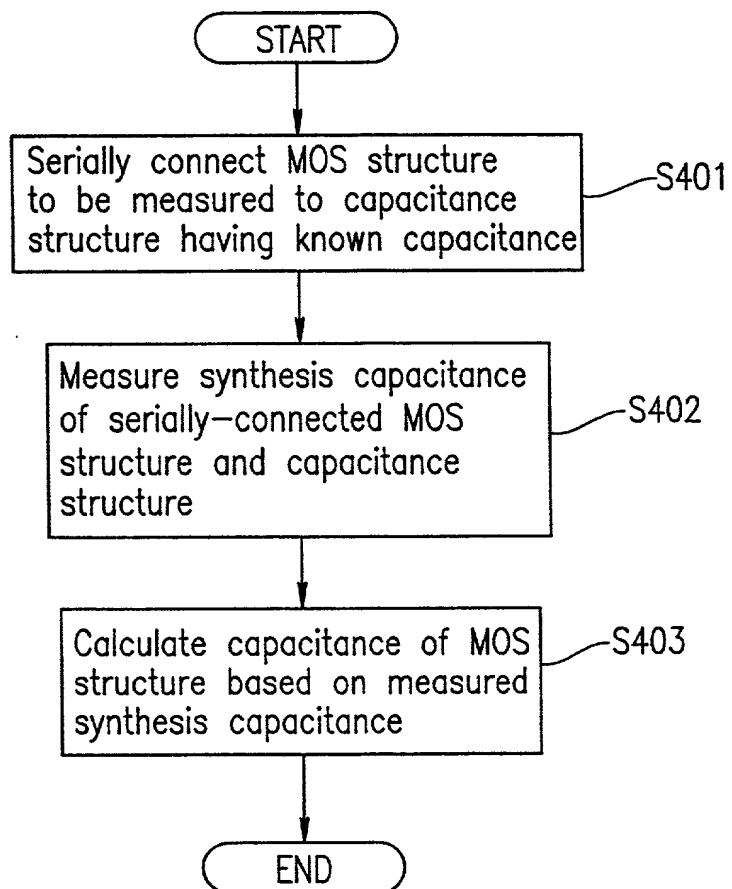
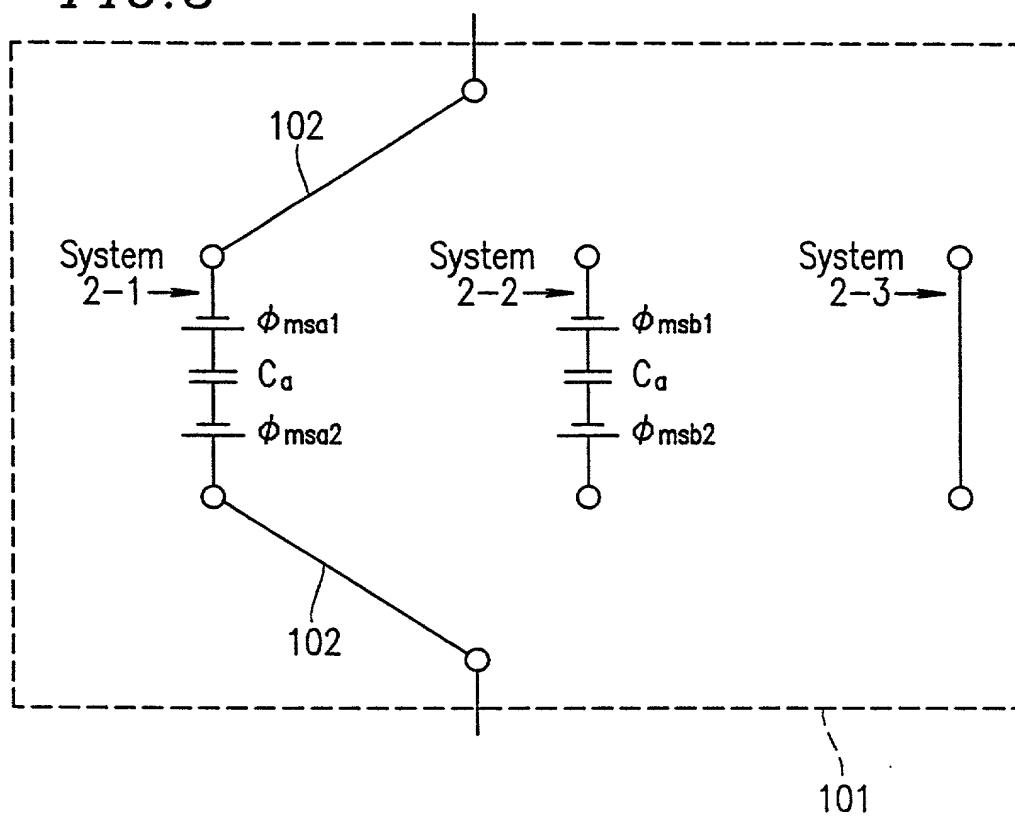


FIG. 4



01R00422

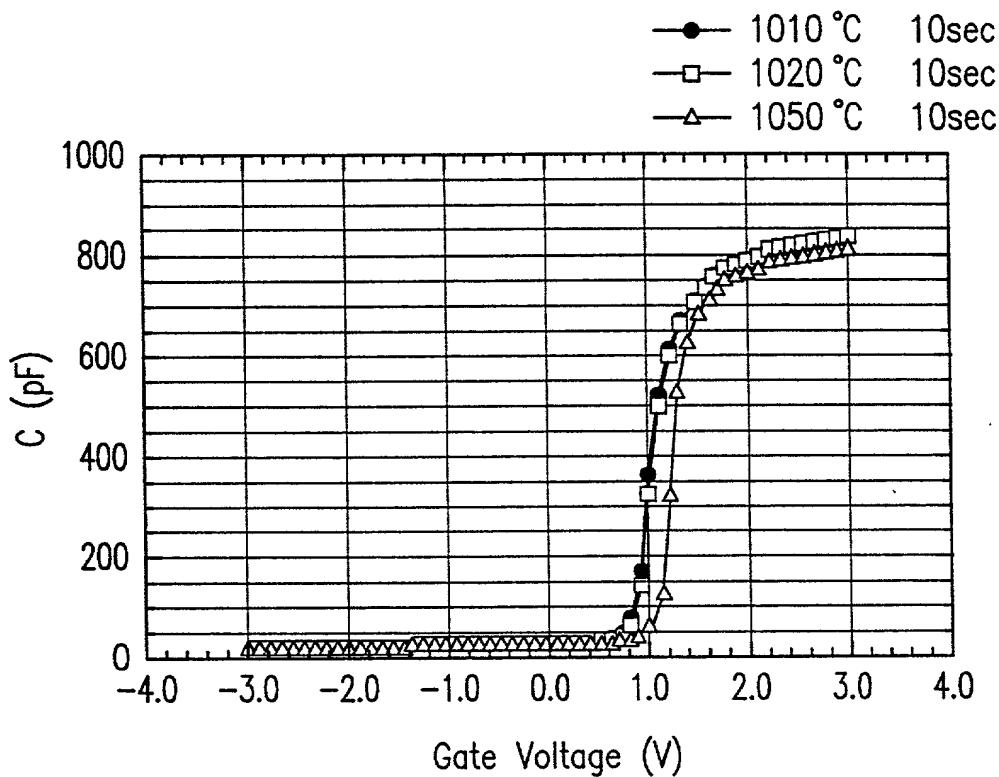
FIG.5



01R00422

FIG. 6

PMOS C-V Characteristics



Active Area: 9E-4cm²
w/o Well Imp.
Gate SiON: NO/N₂

poly Si: 200nm
P+Imp.: BF₂

FIG. 7

NMOS I-V Characteristics

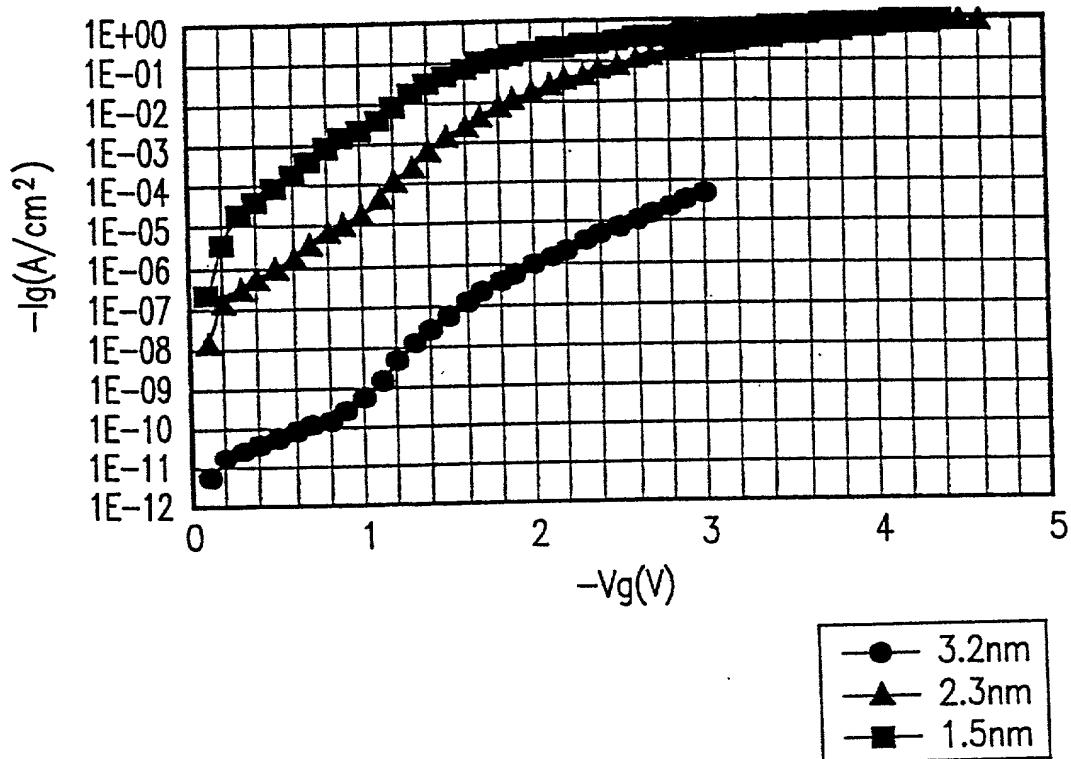
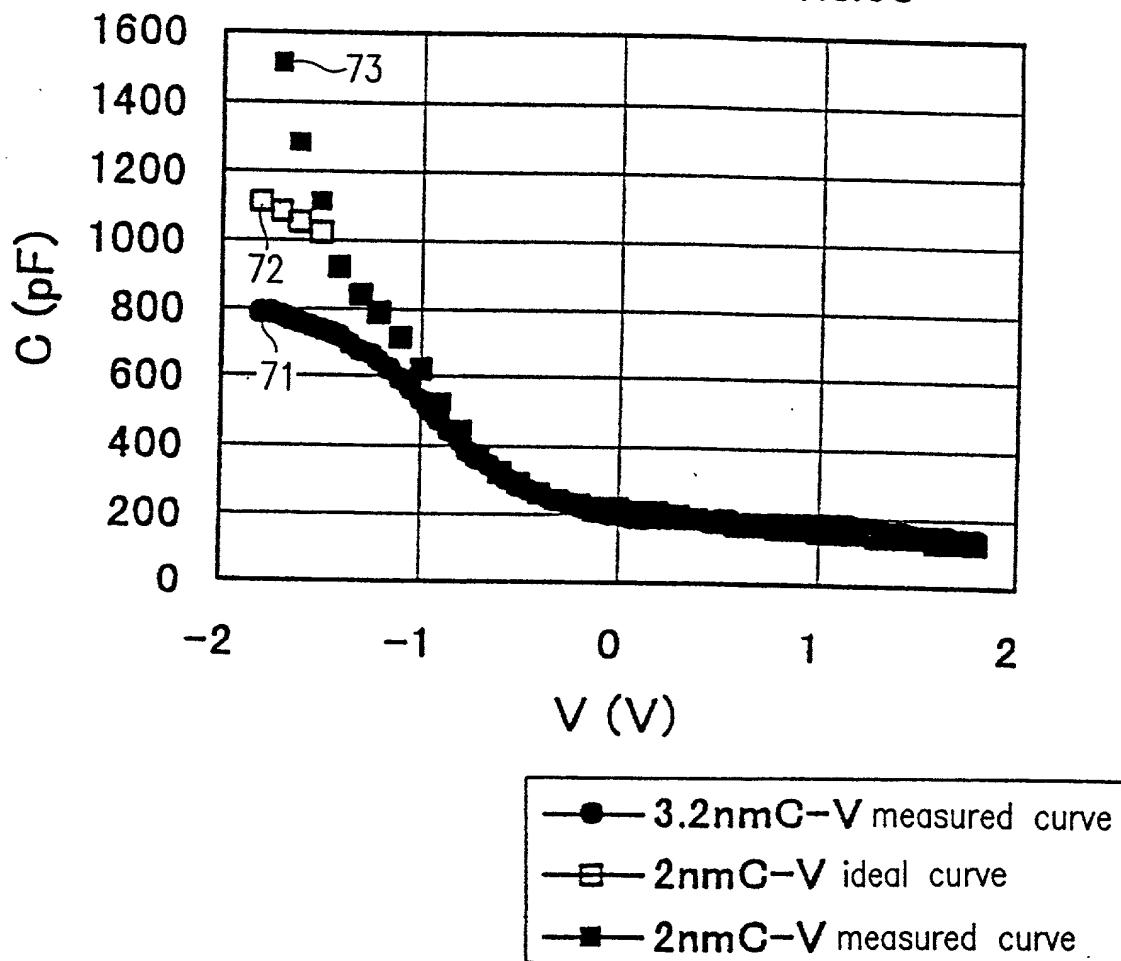


FIG. 8

NMOS C-V Characteristics



01R00422

FIG. 9

